

Supplementary Materials

Neuronal dynamics in $\text{HfO}_x/\text{AlO}_y$ -based homeothermic synaptic memristors with low-power and homogeneous resistive switching

Sungjun Kim,^a Jia Chen,^b Ying-Chen Chen,^c Min-Hwi Kim,^d Hyungjin Kim,^d Min-Woo Kwon,^d Sungmin Hwang,^d Muhammad Ismail,^a Yi Li,^b Xiangshui Miao,^b Yao-Feng Chang,^e and Byung-Gook Park^d

^a School of Electronics Engineering, Chungbuk National University, Cheongju 28644, South Korea

^b School of Optical and Electronic Information & Wuhan National Laboratory for Optoelectronics, Huazhong University of Science and Technology, Wuhan 430074, China

^c Microelectronics Research Center, University of Texas at Austin, Austin, Texas 78758, USA

^d Inter-university Semiconductor Research Center (ISRC) and the Department of Electrical and Computer Engineering, Seoul National University, Seoul 08826, South Korea

^e Intel Corporation, Hillsboro, USA

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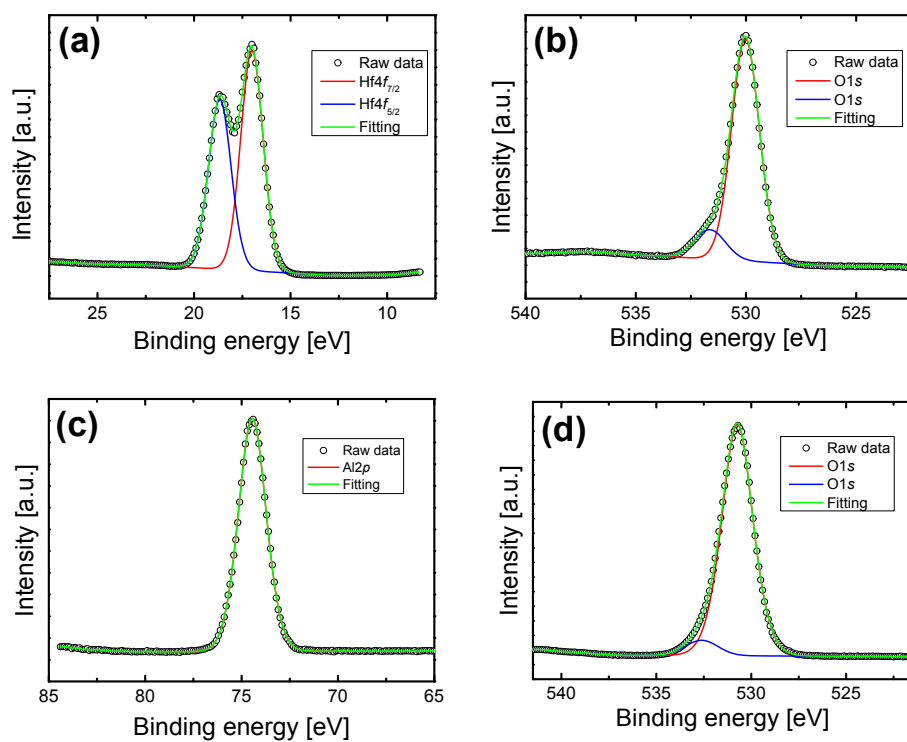


Figure S1

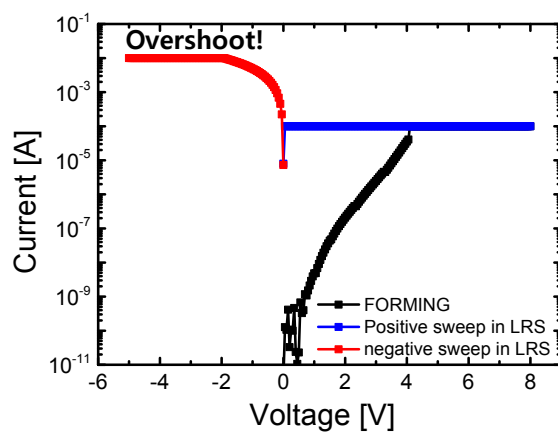


Figure S2

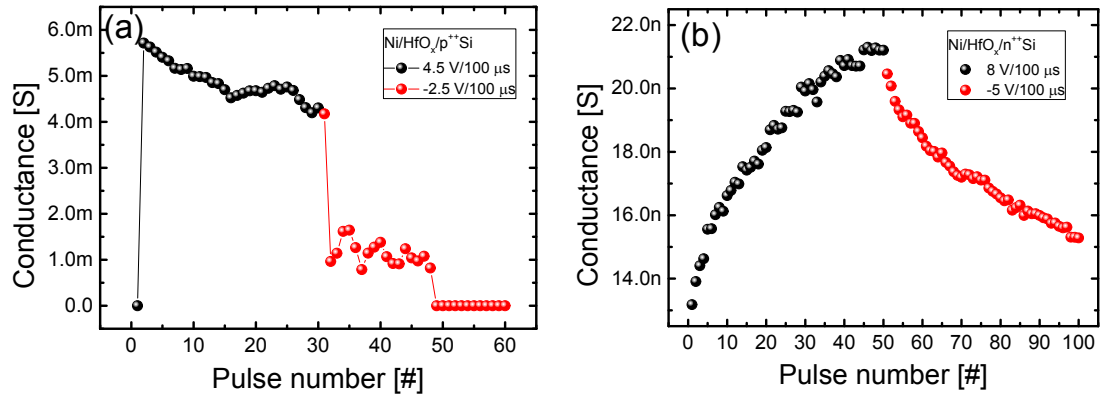


Figure S3

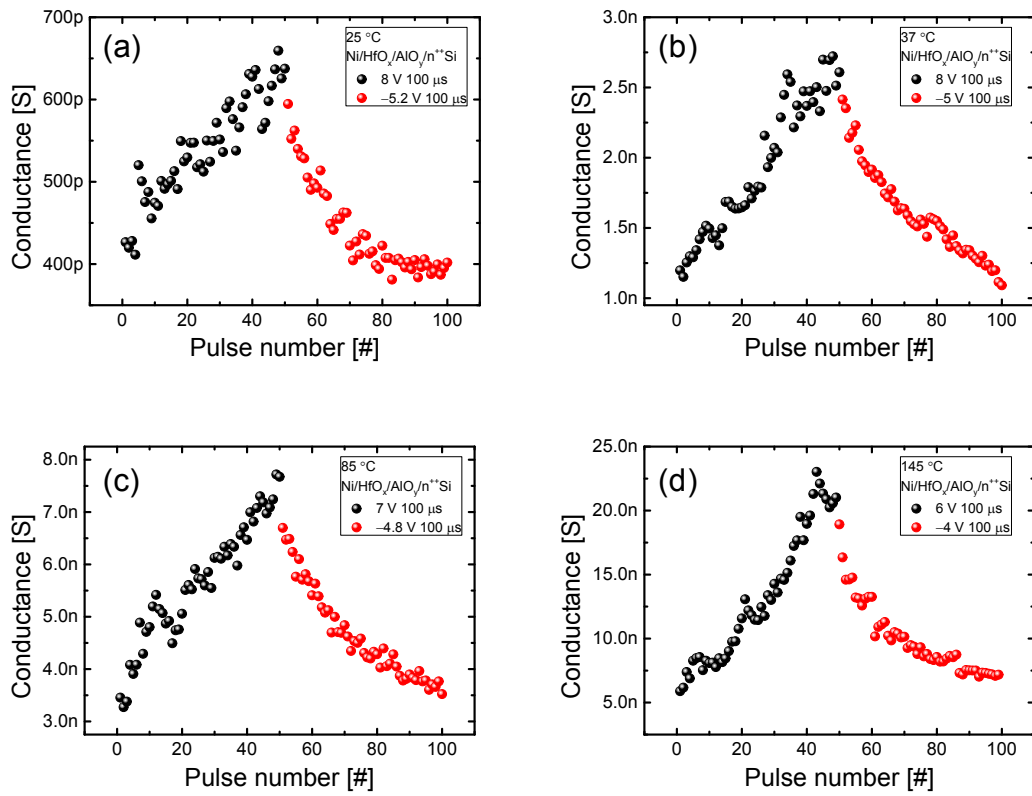


Figure S4

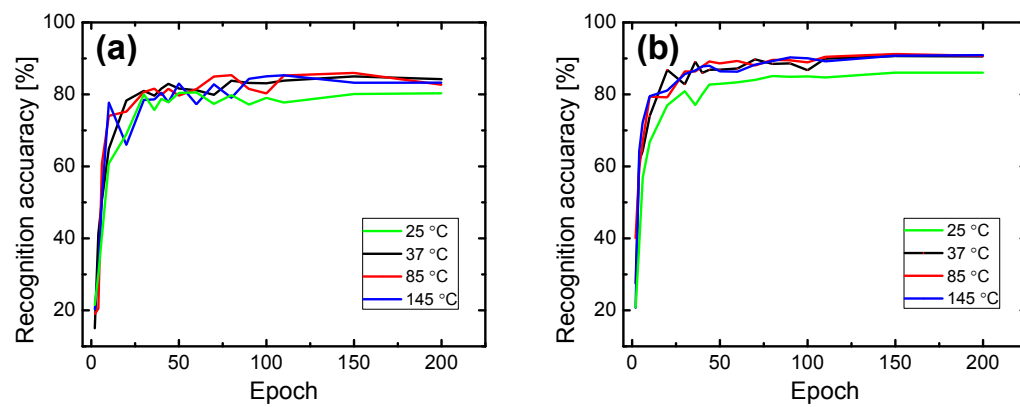


Figure S5